

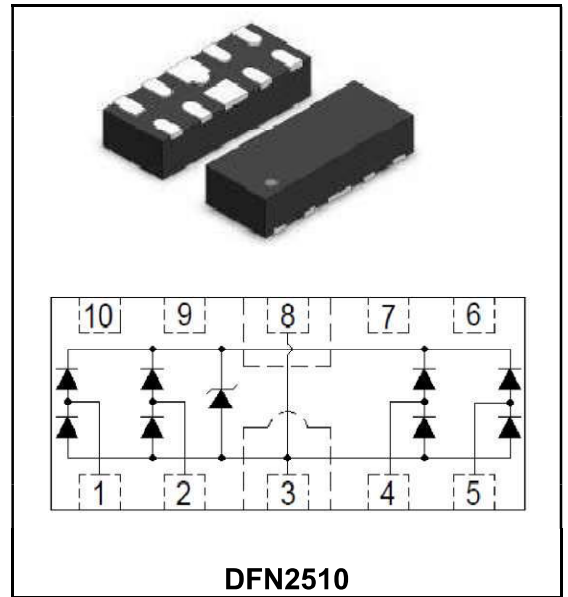
**4 Channel Ultra-low Capacitance
ESD Protection Diode**

Features

- ◆Ultra-Low capacitance:0.45pF(typ.)
- ◆Reverse stand-off voltage:5 V
- ◆IEC 61000-4-2 (ESD Air): ±20kV
- ◆IEC 61000-4-2 (ESD Contact): ±20kV

Application

- ◆USB 3.0, USB 2.0
- ◆HDMI 1.3/1.4, Display Port 1.3, eSATA
- ◆Unified Display Interface (UDI)
- ◆Digital Visual Interface (DVI)
- ◆High speed serial interfaces



Order Information

| Part Number | Package | Marking | Size (mm) | Delivery Form | Delivery Quantity |
|--------------|---------|---------|----------------|---------------|-------------------|
| ESD2510D5V0B | DFN2510 | 0524P | 2.50X1.00X0.50 | 7" T&R | 3000PCS/Tape |

Limiting Values(TA = 25 °C, unless otherwise specified)

| Symbol | Parameter | Conditions | Min | Max | Unit |
|--------|---------------------------------|----------------------------------|-----|-----|------|
| VESD | Electrostatic Discharge Voltage | IEC 61000-4-2; Contact Discharge | - | ±20 | kV |
| | | IEC 61000-4-2; Air Discharge | - | ±20 | kV |
| IPPM | Rated Peak Pulse Current | tP = 8/20 μs | - | 4.5 | A |
| PPP | Peak Pulse Power | tP = 8/20 μs | - | 63 | W |
| TA | Ambient Temperature Range | - | -55 | 125 | °C |
| Tstg | Storage Temperature Range | - | -55 | 150 | °C |

Electrical Characteristics(TA = 25 °C unless otherwise specified)

| Symbol | Parameter | conditions | Min | Typ. | Max | Unit |
|------------------|-------------------------|---|-----|------|-----|------|
| V _{RWM} | Reverse Working Voltage | T _A = 25°C | - | - | 5 | V |
| V _{BR} | Breakdown Voltage | I _R = 1 mA;T _A = 25 °c | 6 | - | - | V |
| I _R | Reverse Leakage current | V _{RWM} = 5V;T _A = 25C | - | - | 100 | nA |
| V _C | Clamping Voltage | I _{pp} =1A,t _p =8/20us,Any I/O to GND , Positive | - | - | 9.8 | V |
| | | I _{pp} =4.5A,t _p =8/20us, Any I/O to GND , Positive | - | - | 14 | V |
| C _L | Junction Capacitance | V _R = 0V, f= 1 MHz,I/O to I/O | - | 0.22 | 0.3 | pF |
| | | V _R = 0V,f= 1 MHz, I/O to GND | - | 0.45 | 0.6 | pF |

Typical Characteristics

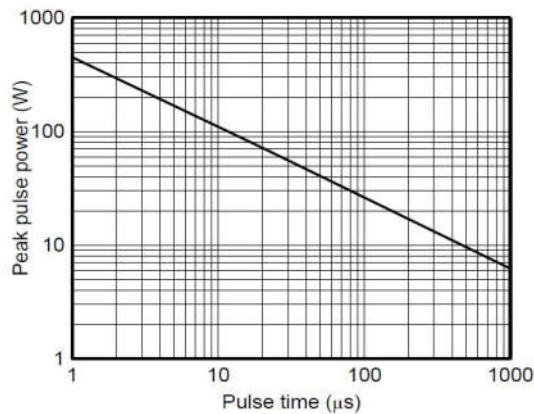


Fig.1 Peak Pulse Power Rating Cure

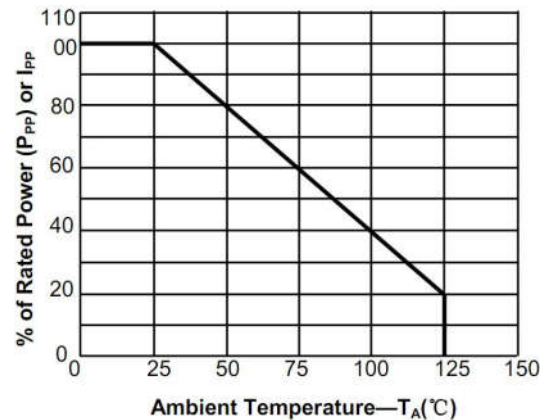


Fig.2 Pulse Derating Curve

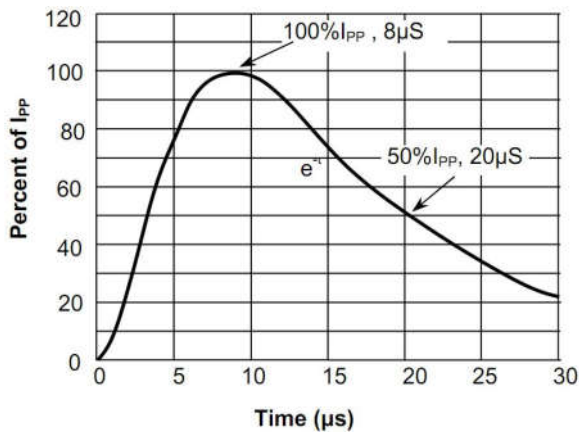


Fig.3 Pulse Waveform- 8/20us

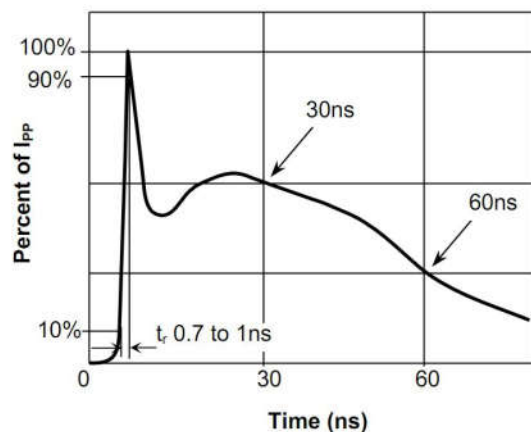
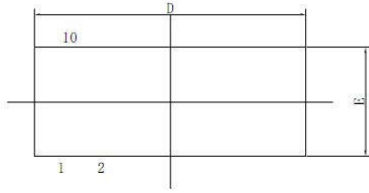
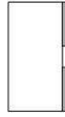


Fig.4 Pulse Waveform-ESD (IEC61000-4-2)

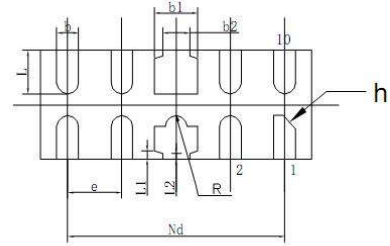
DFN2510 Package Outline



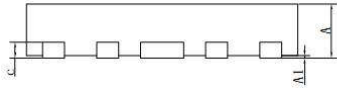
Top View



Side View

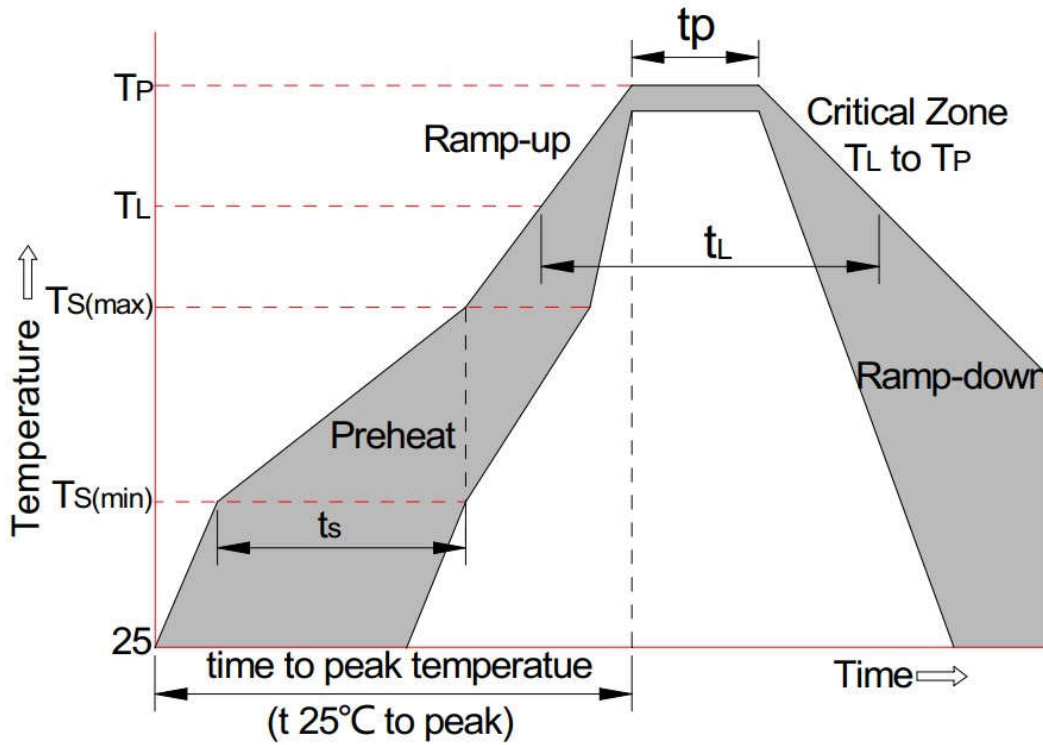


Bottom View



| Symbol | Dimensions in millimeters | | |
|--------|---------------------------|------|------|
| | Min | Nom | Max |
| A | 0.45 | 0.50 | 0.55 |
| A1 | - | 0.02 | 0.05 |
| b | 0.15 | 0.20 | 0.25 |
| b1 | 0.35 | 0.40 | 0.45 |
| b2 | 0.20 | 0.25 | 0.30 |
| c | 0.10 | 0.15 | 0.20 |
| D | 2.45 | 2.50 | 2.55 |
| e | 0.50BSC | | |
| Nd | 2.00BSC | | |
| E | 0.95 | 1.00 | 1.05 |
| L | 0.35 | 0.40 | 0.45 |
| L1 | 0.075REF | | |
| L2 | 0.05REF | | |
| h | 0.08 | 0.12 | 0.15 |
| R | 0.05 | 0.10 | 0.15 |

Soldering Parameters



| Reflow Condition | | Pb-Free Assembly |
|---|-----------------------------------|------------------|
| Pre-heat | -Temperature Min ($T_{s(min)}$) | +150°C |
| | -Temperature Max($T_{s(max)}$) | +200°C |
| | -Time (Min to Max) (t_s) | 60-180 secs. |
| Average ramp up rate (Liquid us Temp (T_L) to peak) | | 3°C/sec. Max |
| $T_{s(max)}$ to T_L - Ramp-up Rate | | 3°C/sec. Max |
| Reflow | -Temperature(T_L)(Liquid us) | +217°C |
| | -Temperature(t_L) | 60-150 secs. |
| Peak Temp (T_p) | | +260(+0/-5)°C |
| Time within 5°C of actual Peak Temp (t_p) | | 30 secs. Max |
| Ramp-down Rate | | 6°C/sec. Max |
| xTime 25°C to Peak Temp (T_P) | | 8 min. Max |
| Do not exceed | | +260°C |